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Synthesis of Ni-poor NiO nanoparticles for DSSC-p applications

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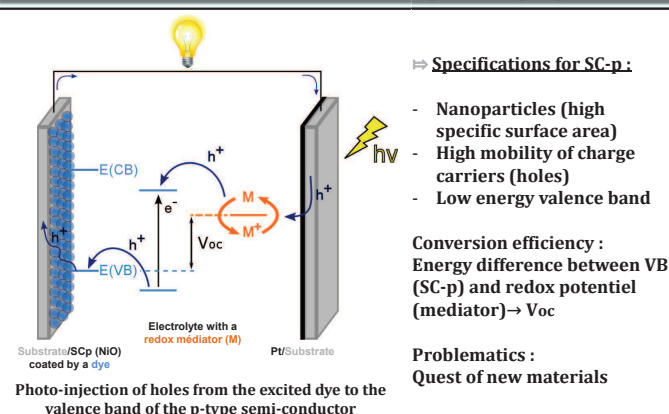
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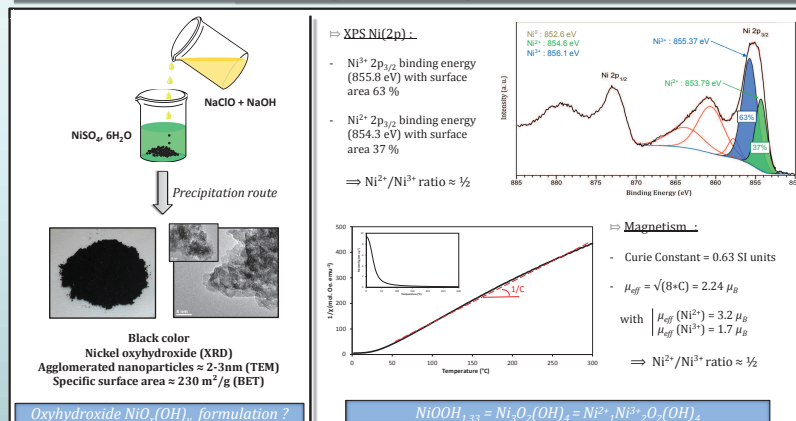
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Over the last decade, p-type semiconductors (SC) have known a renewed interest. Indeed these materials may have potential applications for light-emitting diodes, transistors, solar cells, etc. Since the achievement of the first Dye Sensitized Solar Cells (DSSC) by Grätzel ^[1] in 1991 a new generation of solar cells has been developed ^[2] where the n-type SC is replaced by a p-type one. This leads to the photo-injection of holes instead of electrons in the circuit. To date nickel oxide (NiO) is the reference p-type semiconductor. However yields are still far from those of n-DSSC and many studies aim to replace NiO by other systems such as CuAlO₂, CuGaO₂, CuCrO₂ or NiCo₂O₄ nanoparticles. Following our recent synthesis of N doped ZnO with stabilization of p-type charge carriers ^[3], we focus now on the preparation of N doped NiO nanoparticles to improve the p-type conductivity of NiO. We study here the chemical reactivity of a nickel oxyhydroxide precursor under air and ammonia that conducts to nanostructured Ni-poor NiO ^[4].

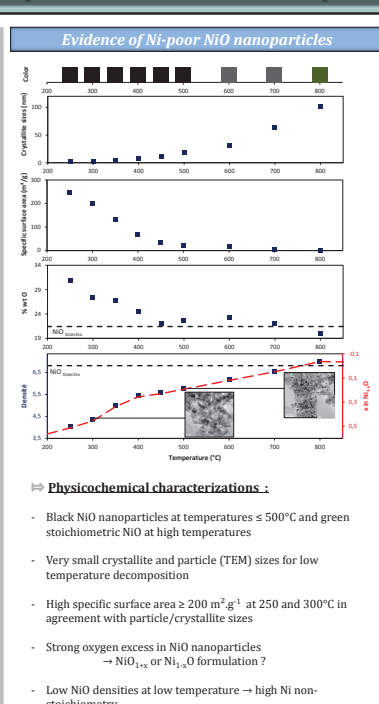
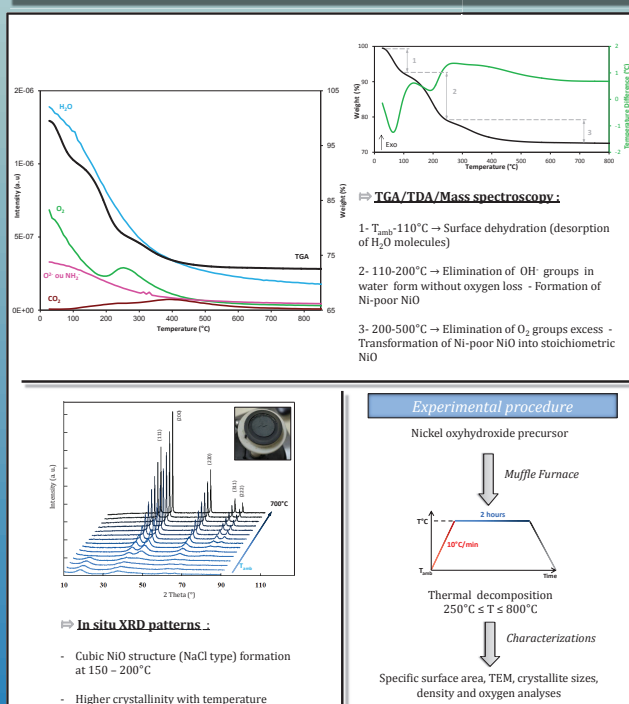
p-DSSC performances



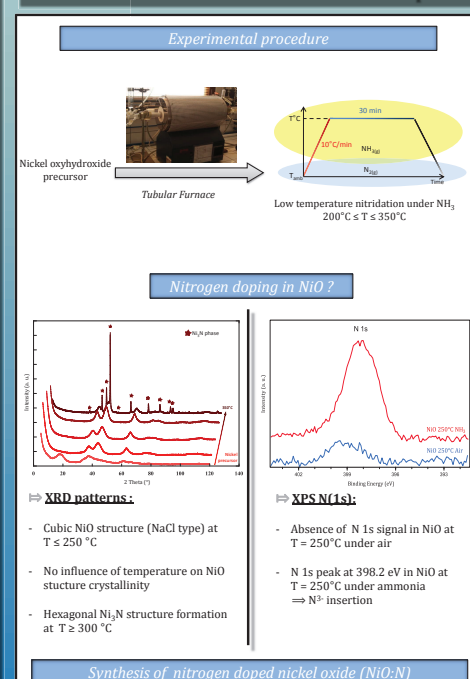
Nickel precursor synthesis & characterizations



Thermal decomposition under air atmosphere



Thermal decomposition under ammonia atmosphere



Conclusion

- ⇒ Synthesis of an original nickel precursor with very small particle sizes and high specific surface area. The determination of the Ni²⁺/Ni³⁺ ratio is leading to the exact formulation Ni₃O₂(OH)₄
- ⇒ Decomposition of Ni₃O₂(OH)₄ under air at temperature lower than 500°C forms strong non-stoichiometric NiO nanoparticles with high nickel vacancy concentration
- ⇒ Stabilization of nitrogen doped NiO by decomposition of Ni₃O₂(OH)₄ under ammonia atmosphere at 250°C
- ⇒ Characterization of Ni-poor NiO and NiO:N nanoparticles in p-DSSC in progress

References

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